

SSC8036GS1

N-Channel Enhancement Mode MOSFET

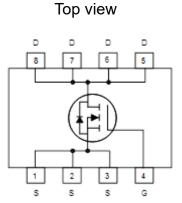
> Features

VDS	VGS	RDSON Typ.	ID	
201/	±20V	20mR@10V	6A	
30V	±20V	30mR@4V5	δA	

> Description

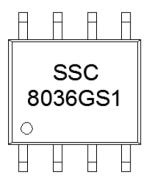
This device uses advanced trench technology to provide excellent RDSON and low gate charge. This device is suitable for use as a load switch or in PWM applications.

Pin configuration





SOP8



Marking

> Applications

- Load Switch
- TFT panel power switch
- DCDC conversion

> Ordering Information

Device	Package	Shipping
SSC8036GS1	SOP8	4000/Reel



> Absolute Maximum Ratings(T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Ratings	Unit	
V _{DSS}	Drain-to-Source Voltage	30	V	
V _{GSS}	Gate-to-Source Voltage	±20	V	
I _D	Continuous Drain Current ^a	6	А	
I _{DM}	Pulsed Drain Current ^b	30	А	
P _D	Power Dissipation °	4	W	
P _{DSM}	Power Dissipation ^a	2	W	
TJ	Operation junction temperature	-55 to 150	°C	
T _{STG}	Storage temperature range	-55 to 150	°C	

> Thermal Resistance Ratings($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
$R_{ heta JA}$	Junction-to-Ambient Thermal Resistance ^a		70	°C /\\
R _{θJC}	Junction-to-Case Thermal Resistance		35	°C/W

Note:

- a. The value of R_{BJA} is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with T_A=25°C. The value in any given application depends on the user is specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.
- c. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

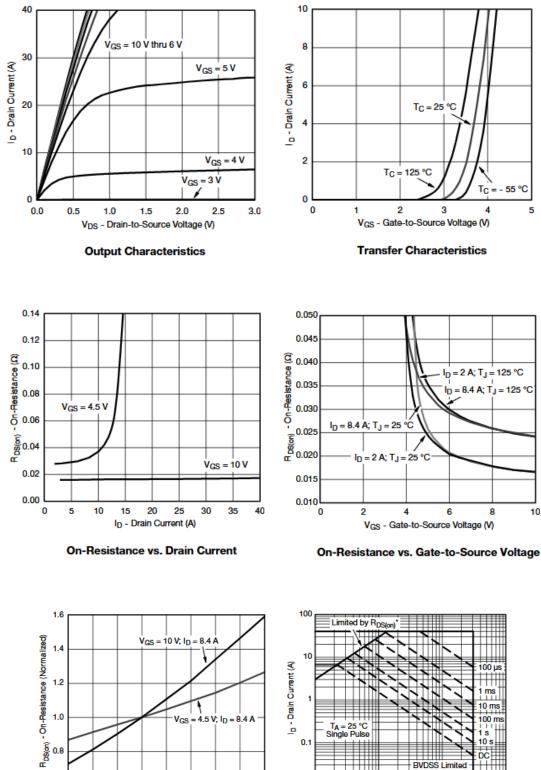


Electronics Characteristics(T_A=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур.	Мах	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage	VGS=0V,ID=250uA	30			V
$V_{GS \ (th)}$	Gate Threshold Voltage	VDS=VGS,ID=250uA	1	1.5	3	V
D	Drain-Source On-	VGS=10V,ID=5.5A		20	28	mR
R _{DS(on)}	Resistance	VGS=4.5V,ID=4.5A		30	43	
I _{DSS}	Zero Gate Voltage Drain Current	VDS=30V,VGS=0V			1	uA
I _{GSS}	Gate-Source leak current	VGS=±20V,VDS=0V			±100	nA
G _{FS}	Transconductance	VDS=5V,ID=5A		12		S
V _{SD}	Forward Voltage	VGS=0V,IS=1A			1.3	V
Ciss	Input Capacitance	VDS=15V, VGS=0V, f=1MHz		490		
Coss	Output Capacitance			86		pF
Crss	Reverse Transfer Capacitance			59		
T _{D(ON)}	Turn-on delay time	VGEN=10V, VDS=15V, RL=15R, RG=3R,ID=1A		18		
Tr	Rise Time			32		- ns
T _{D(OFF)}	Turn-off delay time			16		
Tf	Fall Time			33		
Qg	Total Gate charge	VGS=10V, VDS=10V, ID=4A		10.6		
Qgs	Gate to Source charge			1.9		nC
Qgd	Gate to Drain charge			2.1		

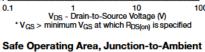


Typical Characteristics(T_A=25°C unless otherwise noted) \triangleright



0.01 - 25 0 25 50 75 100 125 150 0.1 T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature



BVDSS Limited 11111

0.6

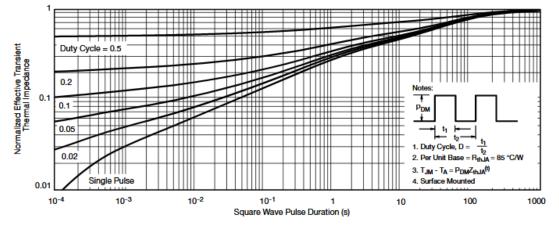
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D

100



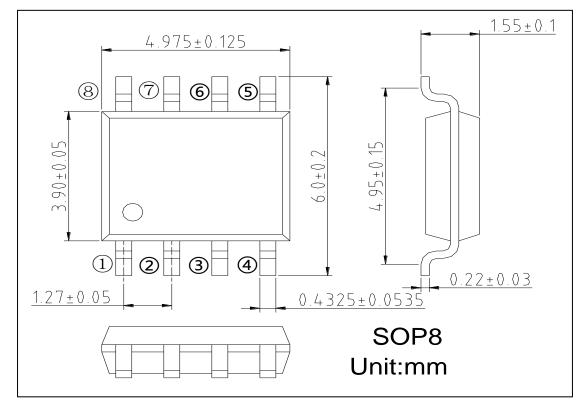
SSC8036GS1



Normalized Thermal Transient Impedance, Junction-to-Ambient



Package Information



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